Greetings from Olaf Vogt

Director and Head of Application Marketing



Olaf Vogt Director and Head of Application Marketing "I would like to thank all participants for joining this first-of-its-kind Nexperia virtual ESD seminar.

The **automotive industry** is driven by the major trends of **electrification**, **autonomous driving and shared 'connected' mobility**.

We also see that ever-increasing data rates, greater calculation power of System-on-Chips and IC miniaturization are making **systems even more sensitive to ESD**.

With our Nexperia ESD Seminar, we want to **support the design community** in protecting applications and products against ESD issues and make systems more reliable.

Additionally, we published an **automotive ESD** application handbook to share our expertise and best practices with you."

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APPLICATION HANDBOOK **AUTOMOTIVE** EDTON **PROTECTION CONCEPTS**, **TESTING & SIMULATION FOR** MODERN INTERFACES Design Engineer's Guide





Nexperia ESD Seminar Session 2 ESD Protection for Automotive Interfaces

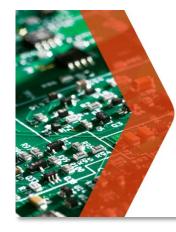
Dr. Andreas Hardock

Application Marketing Manager for ESD and EMC <u>andreas.hardock@nexperia.com</u>

Lukas Droemer

Product Manager Automotive ESD Protection & Filtering <u>lukas.droemer@nexperia.com</u>

Recap | Nexperia ESD Seminar Session 1



Selection Criterion

Selection Criteria: Number of signal lines

nexperia **Nexperia ESD Seminar Session 1** Fundamentals of ESD Protection ESD – Electro Static Discharge WHAT A sudden discharge between persons, devices or components HOW A charged person touches an integrated circuit (IC) · A charged IC drops on a grounded metal plate · A charged machine touches an IC etallisation or PN junctions Single signal line vs. multiple similar lines, e.g. USB 3.0

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ESD – Dynamic Resistance Typical pulse width 100 ns VF-TLP (very fast) ~3 ns

In session 1, we talked about:

- **Fundamentals of ESD Protection** •
 - ESD protection background •
 - Device vs. system level perspective •
 - Impact and trends .
- **Measurement and Characterization**
- Selection Criterion •
- **ESD** Tolerance Test ٠
- Clamping Voltage .
- Dynamic Resistance using TLP .
- Zener and Snapback .

In session 2, we will learn how to apply the concept of ESD protection with common automotive interfaces.

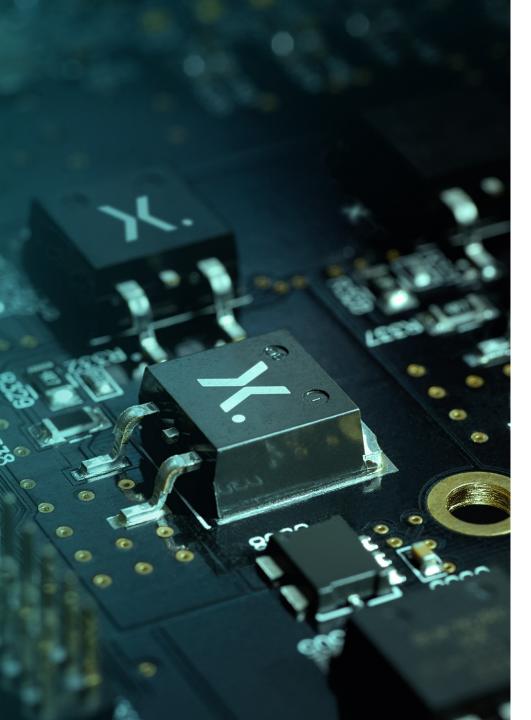


USB 2.0 -

USB3.1 SSRX-

SSTX+ SSTX-USB 3.0/ SSRX+

GND

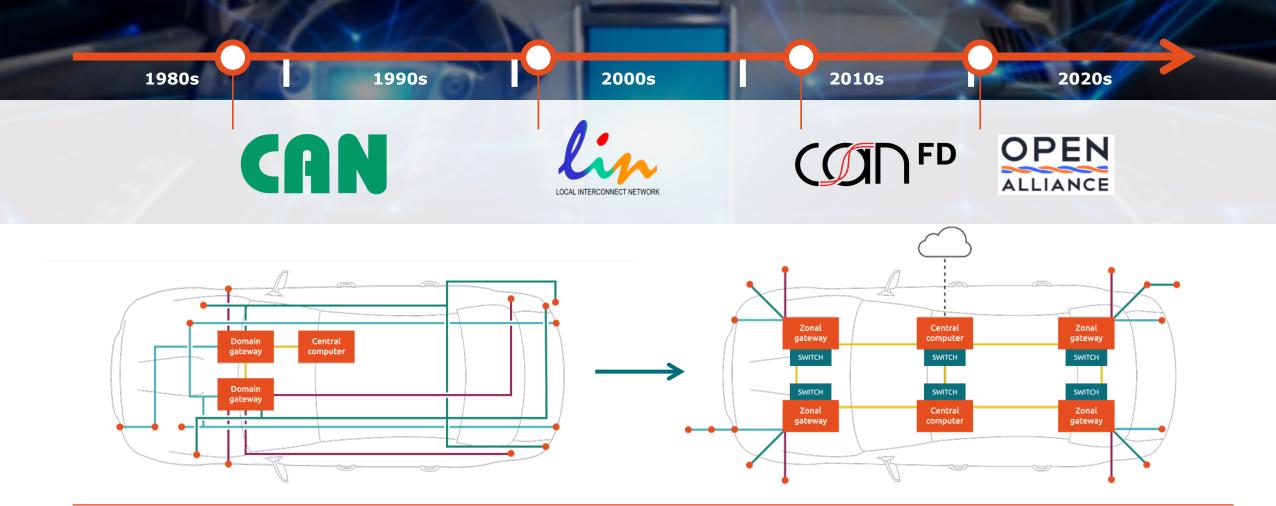


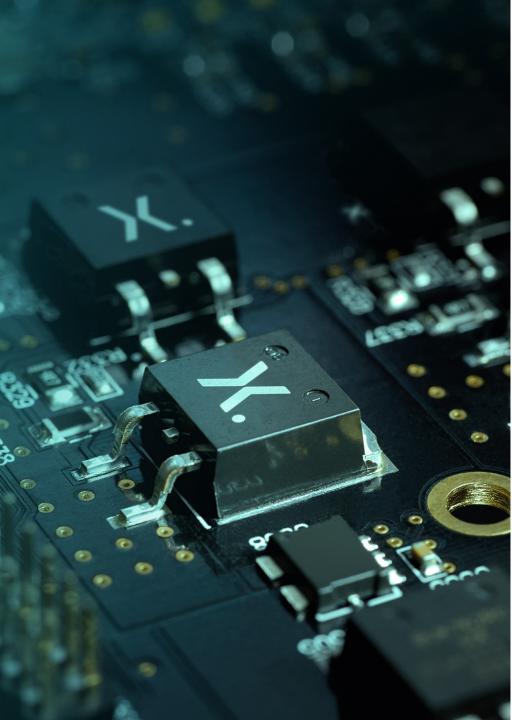
ESD Seminar Session 2

Agenda

- Classic in-vehicle networks
- OPEN Alliance Ethernet
- SerDes
- Infotainment/Multimedia
- Extra: Package aspects
- Q&A

Evolution of In-Vehicle Networking





ESD Seminar Session 2

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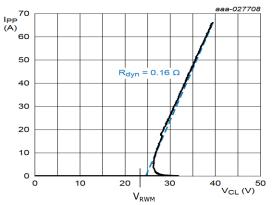
LIN Local Interconnect Network

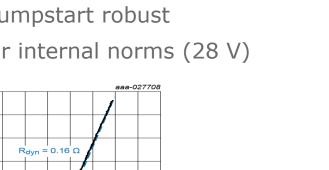


Requirement for ESD protection depend on OEM

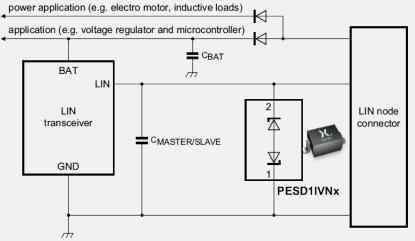
Sometimes only specific devices are approved, most of the time, just general requirements to the interface exist

- Common requirements:
 - Parasitic capacitance of 30-100pF max
 - Short-to-battery and jumpstart robust
 - ISO16750-2 (26 V) or internal norms (28 V)















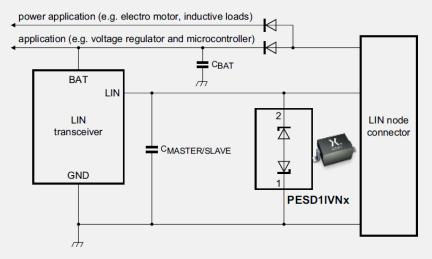
Compliance with ISO17987 in combination with a transceiver

• ESD

- RF emission
- immunity to transients -> ISO7637-2 (3a/b)
- RF immunity -> DPI

[dBm] 40 35 — Max. Test power 30 Limit 25 - CW **DPI Test LIN** 20 TJA1021T Transceiver: Unwanted wake-up via LIN (#2f) Test case: sleep / CP1 (LIN) Mode / coupling: 15 Failure validation: INH Bus filter: C = 3 x 68pF, 1 x PESD1IVN24-A 10 . [MHz] 10 100 1000







006aaa678



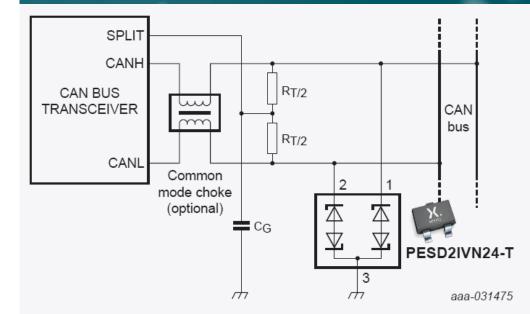


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• Requirement for ESD protection depend on OEM

Sometimes only specific devices are approved, most of the time, just general requirements to the interface exist

- Common requirements:
 - Parasitic capacitance of 17-30pF max
 - (for CAN FD 6-10)
 - Because of rather high Cp, matching is required
 - Short-to-battery and jumpstart robust
 - ISO16750-2 (26 V) or internal norms (28 V)



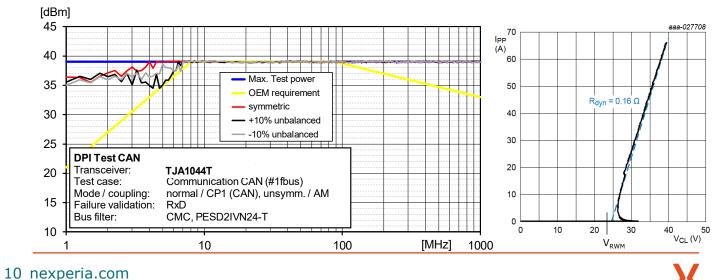


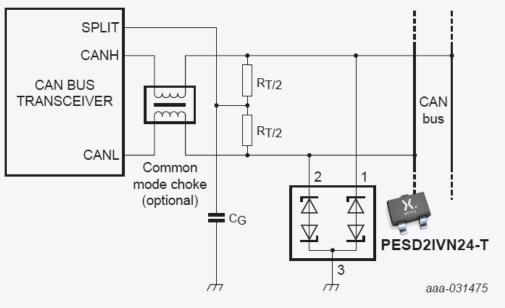




Compliance with IEC62228-3 in combination with a transceiver

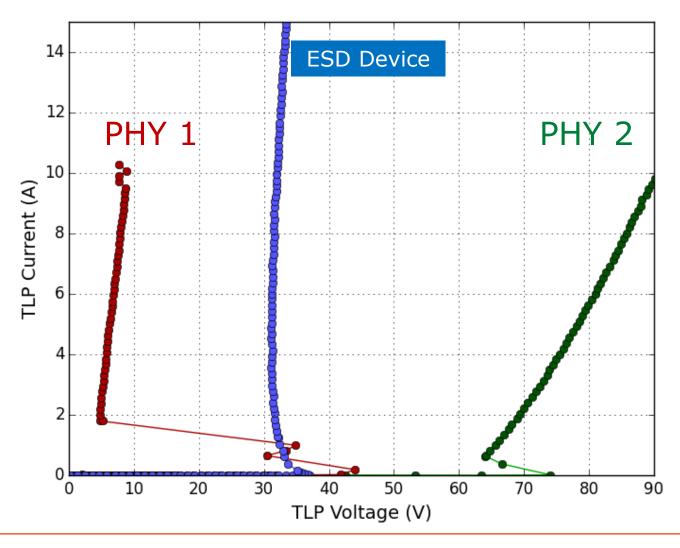
- ESD
- RF emission
- immunity to transients -> ISO7637-2 (3a/b)
- RF immunity -> DPI



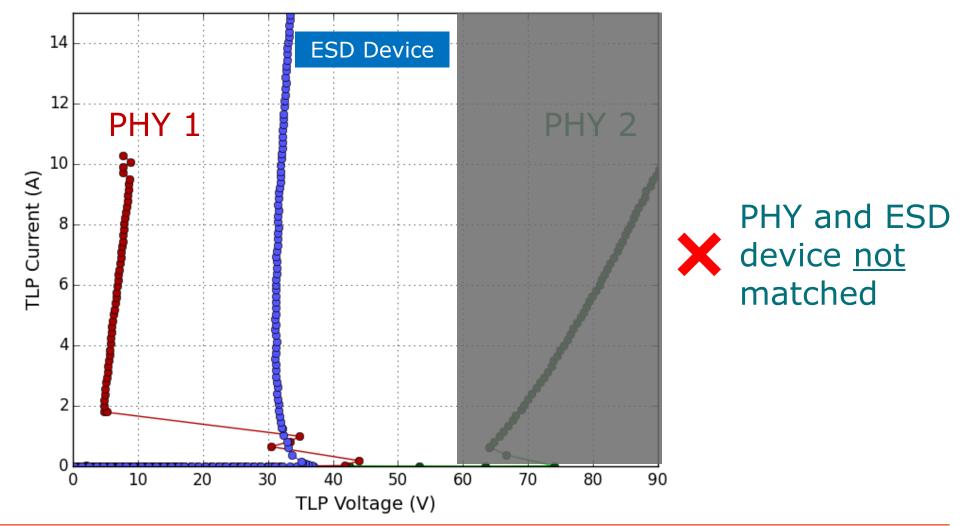




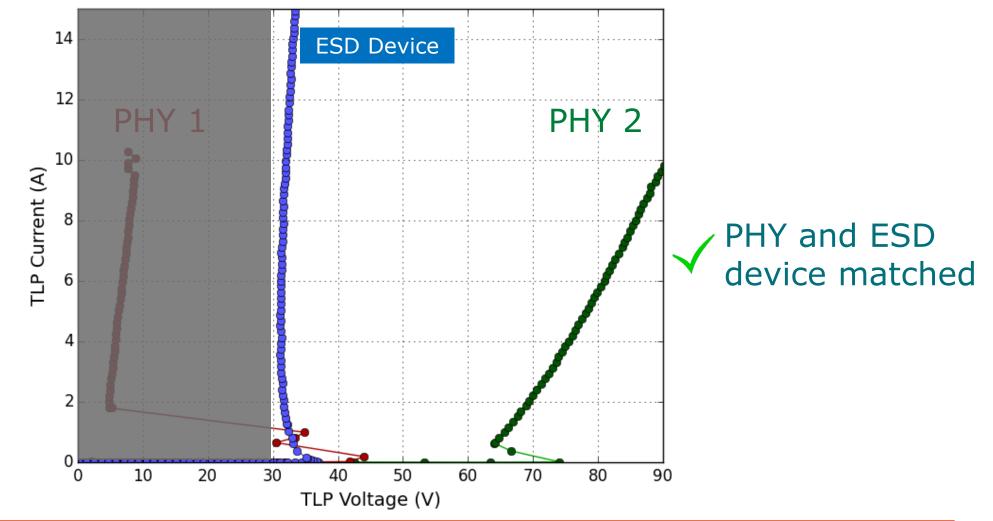
Example CAN Device vs. System Robustness

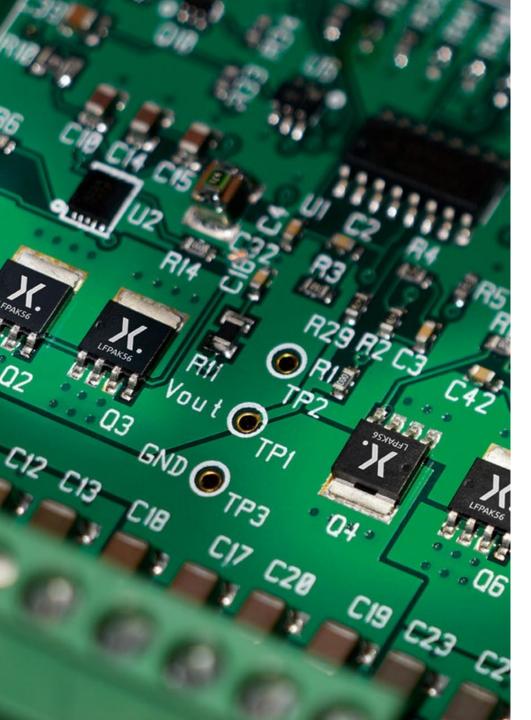


Example CAN Device vs. System Robustness



Example CAN Device vs. System Robustness

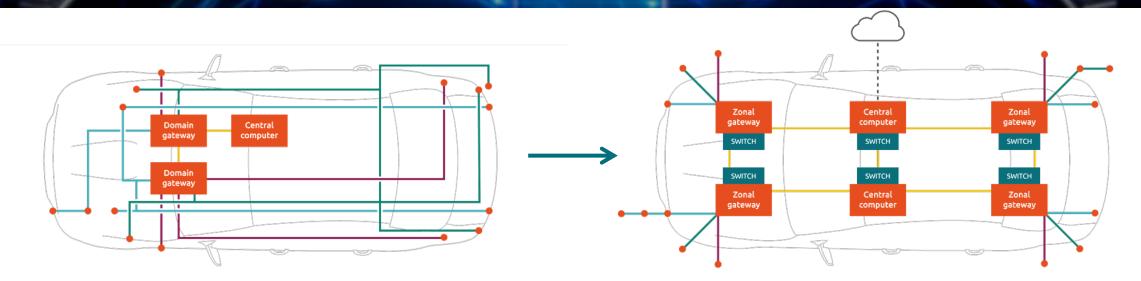




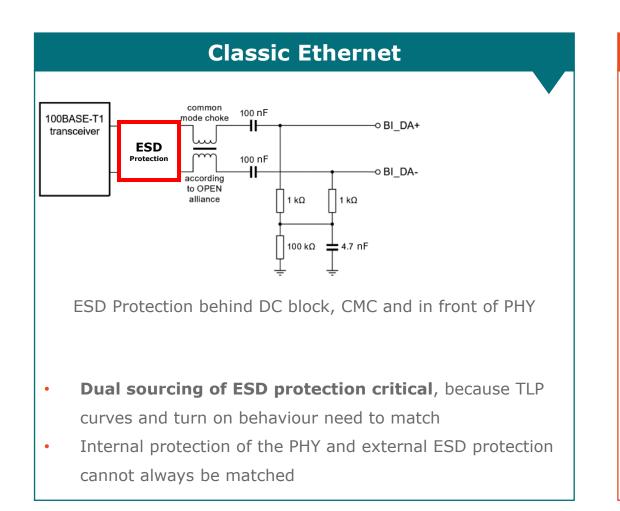
ESD Seminar Session 2 Agenda

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- OPEN Alliance Ethernet
- SerDes
- Infotainment/Multimedia
- Extra: Package aspects
- Q&A

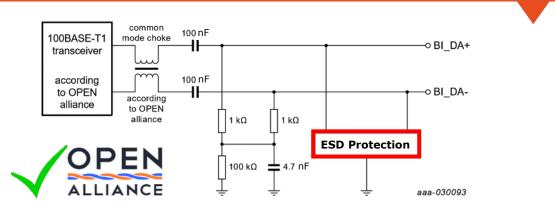
Automotive Ethernet requires the transition from traditional to domain and zonal architectures to support our shared vision of automotive future.



Classic Ethernet vs. OPEN Alliance



OPEN Alliance Ethernet



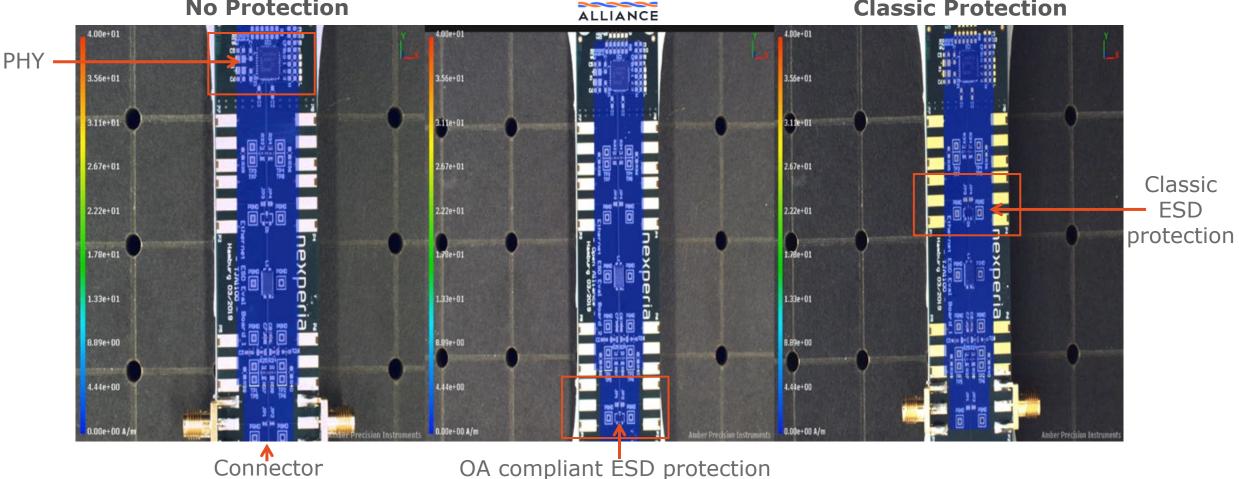
ESD Protection in front of DC Block, CMC and PHY

- **Dual sourcing of ESD protection uncritical**, because ESD protection in front of DC block and CMC protect whole system
- External ESD protection is decoupled from internal protection of the PHY. **PESD2ETH1G-T matches with every PHY**

100BASE-T1 concept comparison

Comparison of ESD protection concepts evaluated by EMI scanner

No Protection



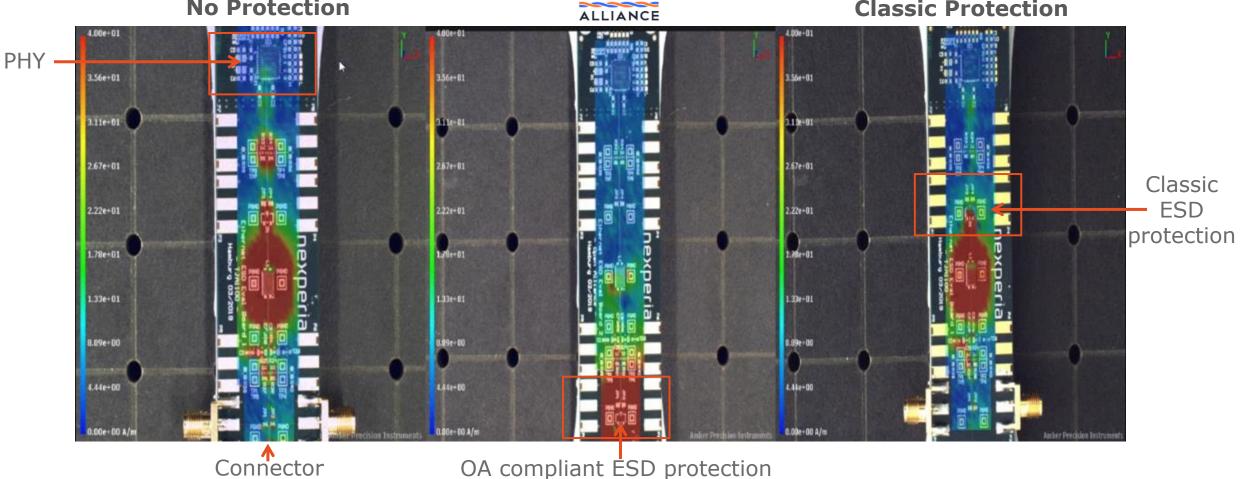
OPEN

Classic Protection

100BASE-T1 concept comparison

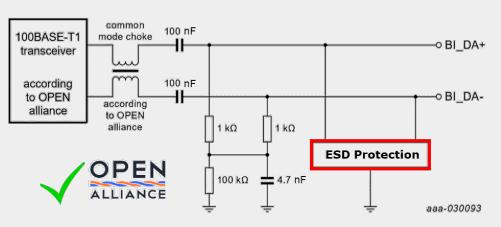
Comparison of ESD protection concepts evaluated by EMI scanner OPEN

No Protection



Classic Protection



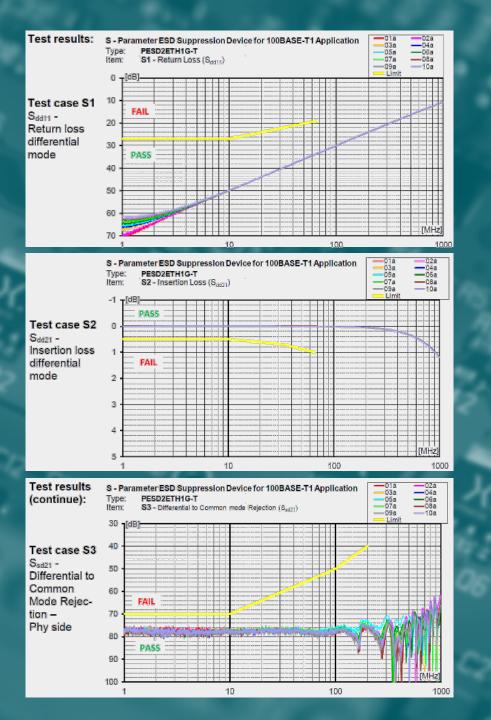




General requirements

General requirements

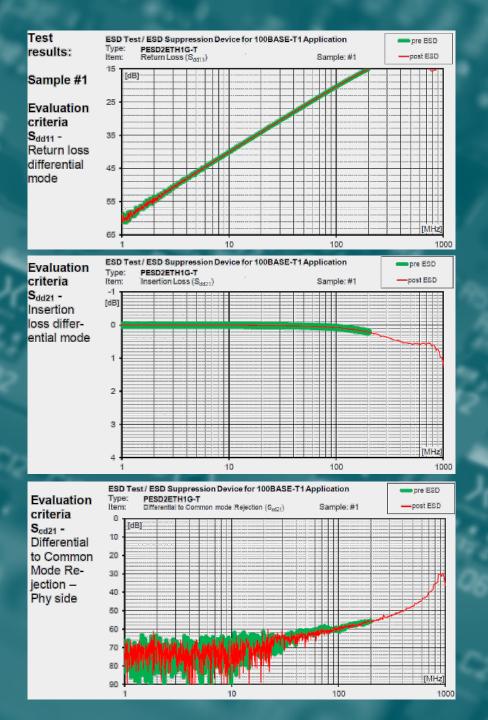
- Trigger voltage > 100V, V_{DC,max} > 24V
- Bi-direction device, 15kV IEC, 1000 discharges
- Additional tests
 - Mixed mode S-parameter measurements
 - To evaluate transmission, symmetry, and mode conversion, replaces requirements on $C_{\rm p}$ and matching
- Damage from ESD
 - To verify degradation, first measure S-parameters, apply ESD (8kV) discharges, and check S-parameters again
- ESD discharge current measurement
 - Quantification of the current that would flow into the PHY
- Unwanted clamping
 - Evaluate impact of ESD device onto RF immunity testing



Mixed mode S-parameter measurements

• General requirements

- Bi-direction device, 15kV IEC, 1000 discharges
- Trigger voltage > 100V, $V_{DC,max}$ > 24V
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Damage from ESD

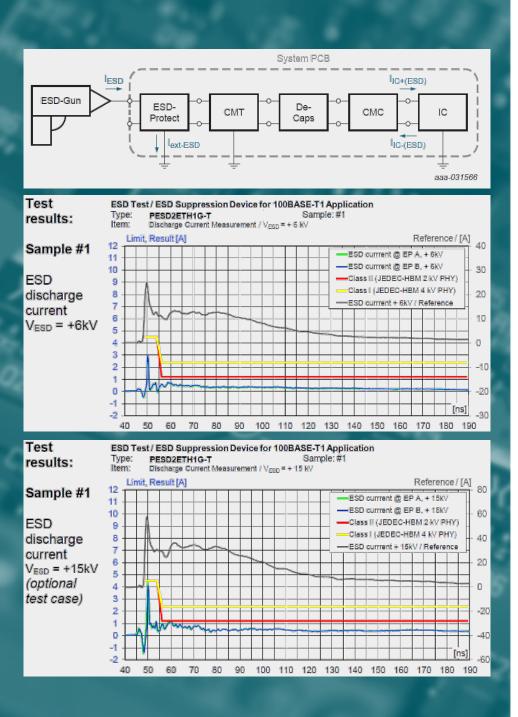
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ESD discharge current measurement

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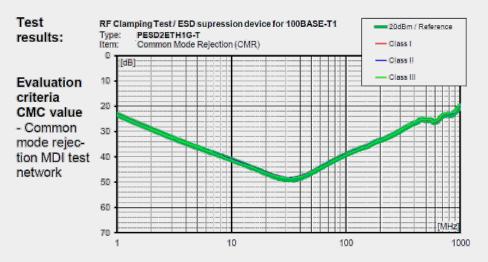
Additional tests

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• ESD discharge current measurement

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Unwanted clamping

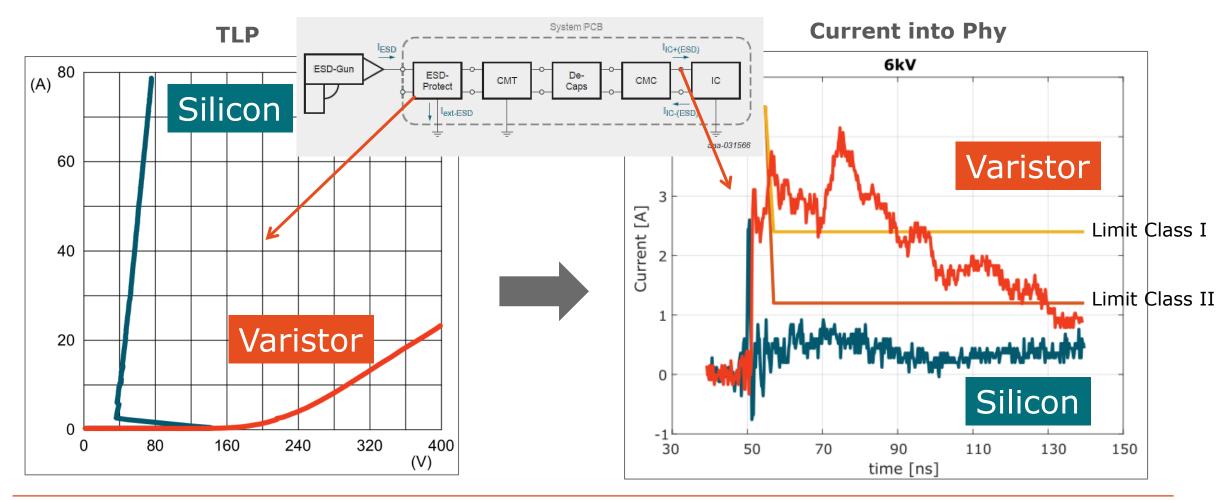
- General requirements
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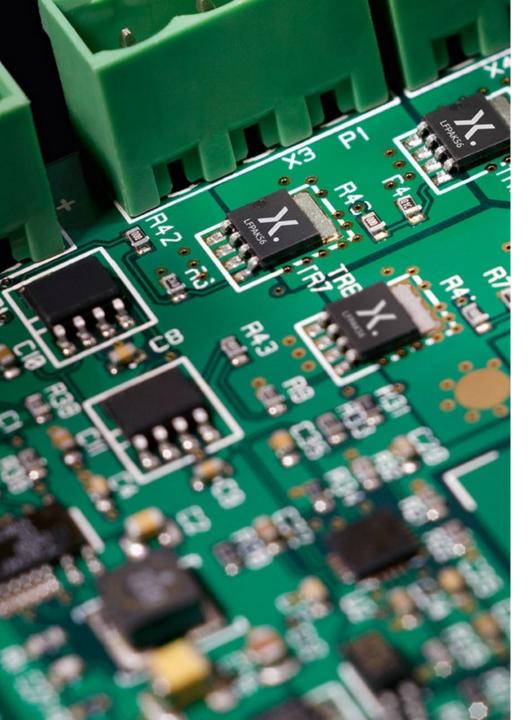
Additional tests

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ESD Discharge Current Measurement

Clamping performance and system robustness





ESD Seminar Session 2

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In 2019, **82% of vehicles** sold featured a touch screen, compared to 53% five years ago.

By 2030, the average car will have ~20 cameras and ~15 displays per vehicle.

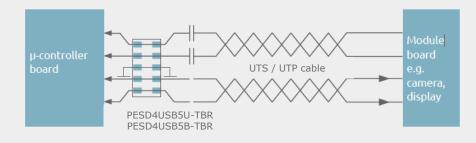
Brunner & Gauthier | ASA



LVDS physical layer

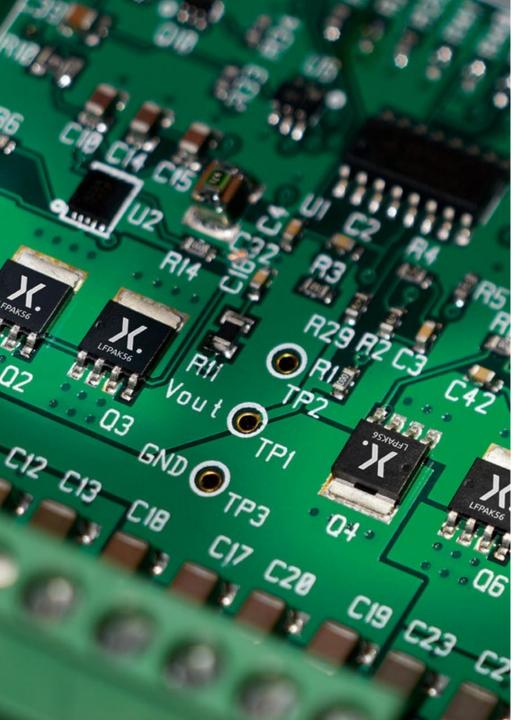
- Many propriatary systems. No open standards and different handling by OEMs and IC vendors.
- Max parasitic capacitance depends on datarate
 - Usually, should be very low Cp < 1pF
 - Matching of lines usually not required, as Cp is very small
- Short-to-battery and jumpstart are not considered
- The lower the clamping voltage, the better is the protection.
- The protection should be as close as possible at the connector
- Leadless packages help to reduce parasitics







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ESD Seminar Session 2 Agenda

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Infotainment

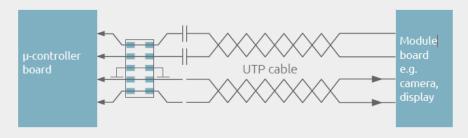
Common infotainment busses

USB - Universal **S**erial **B**us

HDMI - High **D**efinition **M**ultimedia **I**nterface

- Very low capacitance mandatory <<1pF
- RF compliance via
 - S-parameters
 - Eye diagrams
 - TDR
- Very low clamping required to protect sensitive ICs
- Fast turn-on required to prevent dynamic overshoot





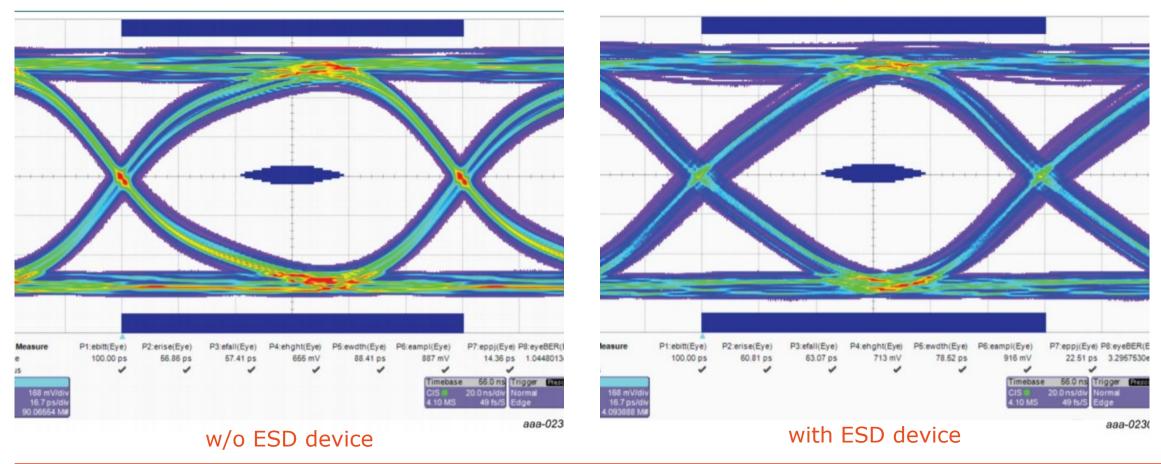
PESD4USB3U-TBR

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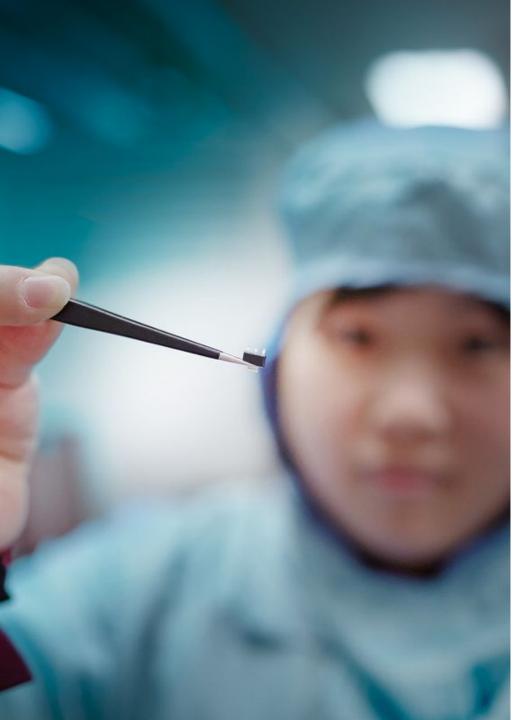


Signal integrity importance

Eye diagramm



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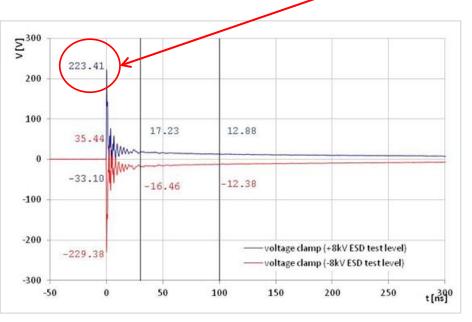
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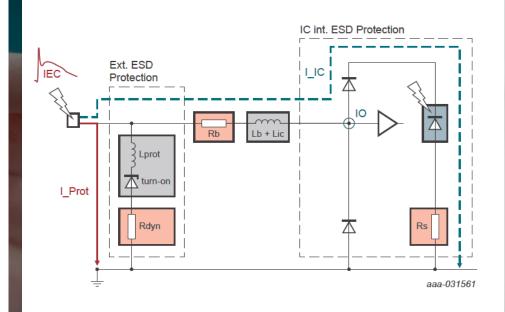
Package aspects – Clamping behavior

For high-speed busses

- Rdyn governs the clamping voltage in a quasi-static condition
- The dynamic behavior is determined by inductances and turn-on behavior





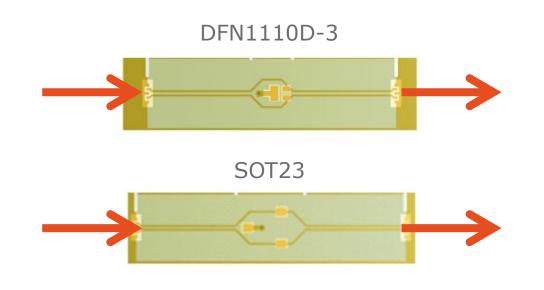


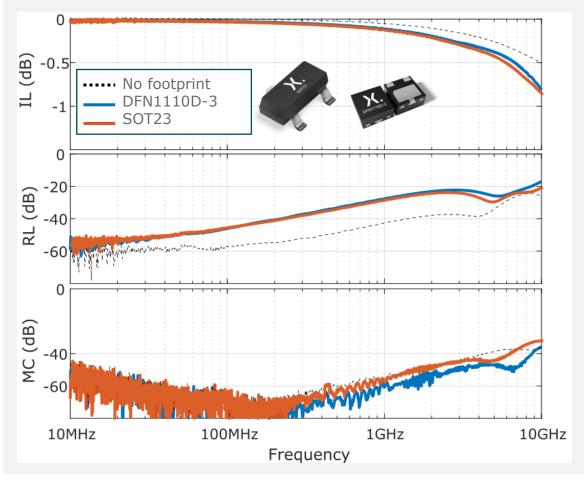


Package aspects – RF behavior

Comparison of SOT23 and DFN1110D-3 only footprint

- Ca. 2 cm traces on FR4
- Dashed line: no footprint
- No big difference between footprints

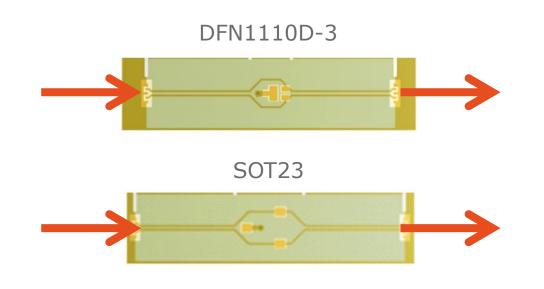


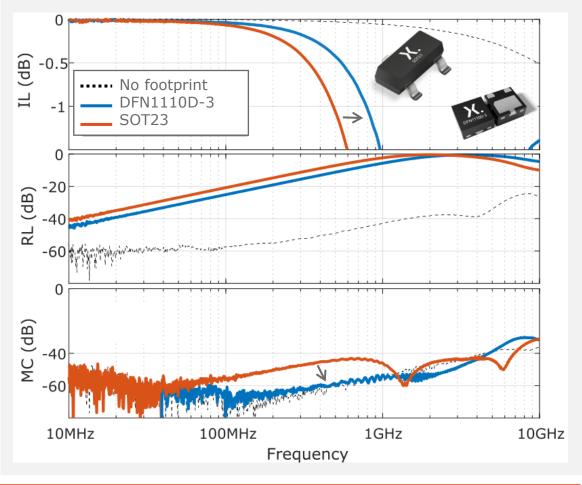


Package aspects – RF behavior

Comparison of SOT23 and DFN1110D-3 with PESD2CANFD24V ($C_p = 5.2 \text{ pF}$)

- Ca. 2 cm traces on FR4
- Dashed line: no footprint
- Clear advantage of leadless package





Service & Support

Find out more about Nexperia and our products & services





ESD for Electronic Design Engineers Seminar

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EFFICIENCY WINS.



EFFICIENCY WINS.